COMPLIANT

HALOGEN

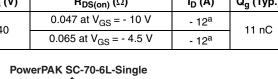
FREE

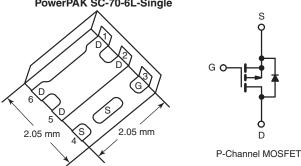


# Vishay Siliconix

# P-Channel 40 V (D-S) MOSFET

PRODUCT SUMMARY								
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ.)					
- 40	0.047 at V <sub>GS</sub> = - 10 V	- 12 <sup>a</sup>	11 nC					
	0.065 at V <sub>GS</sub> = - 4.5 V	- 12 <sup>a</sup>	11110					





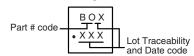
### **FEATURES**

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- Thermally Enhanced PowerPAK® SC-70 Package
  - Small Footprint Area
  - Low On-Resistance
- 100 %  $\rm R_{\rm g}$  and UIS Tested
- Compliant to RoHS Directive 2002/95/EC

### **APPLICATIONS**

- Portable and Consumer Devices
  - Load Switch
  - DC/DC Converter
  - Motor Drive
  - High-Side Switch in Half- and Full-Bridge Converters

## **Marking Code**



### **Ordering Information:**

SiA441DJ-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS	( ) A 20 0, a.m.					
Parameter		Symbol	Limit	Unit		
Drain-Source Voltage		V <sub>DS</sub>	- 40	V		
Gate-Source Voltage		V <sub>GS</sub>	± 20	v		
	T <sub>C</sub> = 25 °C		- 12 <sup>a</sup>			
Continuous Drain Current (T <sub>.I</sub> = 150 °C)	T <sub>C</sub> = 70 °C	L	- 12 <sup>a</sup>			
Continuous Diain Current (1) = 130 °C)	T <sub>A</sub> = 25 °C	I <sub>D</sub>	- 6.6 <sup>b, c</sup>			
	T <sub>A</sub> = 70 °C		- 5.3 <sup>b, c</sup>	A		
Pulsed Drain Current (t = 300 μs)	1	I <sub>DM</sub>	- 30	_ ^		
Continuous Source-Drain Diode Current	T <sub>C</sub> = 25 °C	I.	- 12 <sup>a</sup>			
Continuous Source-Drain Diode Current	T <sub>A</sub> = 25 °C	Is —	- 2.9 <sup>b, c</sup>			
Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	13			
Single Pulse Avalanche Energy	L = 0.1 IIII	E <sub>AS</sub>	8.5	mJ		
	T <sub>C</sub> = 25 °C		19			
Maniana Pausa Dissination	T <sub>C</sub> = 70 °C	P <sub>D</sub>	12	w		
Maximum Power Dissipation	T <sub>A</sub> = 25 °C	' D	3.5 <sup>b, c</sup>	VV		
	T <sub>A</sub> = 70 °C		2.2 <sup>b, c</sup>			
Operating Junction and Storage Temperature Ra	ange	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C		
Soldering Recommendations (Peak Temperature	e) <sup>d, e</sup>	Ü	260			

THERMAL RESISTANCE RATINGS									
Parameter		Symbol	Typical	Maximum	Unit				
Maximum Junction-to-Ambient <sup>b, f</sup>	t ≤ 5 s	R <sub>thJA</sub>	28	36	°C/W				
Maximum Junction-to-Case (Drain)	Steady State	$R_{thJC}$	5.3	6.5	O/ VV				

### Notes:

- a. Package limited.
- b. Surface Mounted on 1" x 1" FR4 board.
- d. See Solder Profile (www.vishay.com/doc?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.
- f. Maximum under Steady State conditions is 80 °C/W.

Document Number: 63277 S11-1183-Rev. A, 13-Jun-11



<b>SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C, unless otherwise noted)									
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit			
Static									
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0$ , $I_{D} = -250 \mu A$	- 40			V			
V <sub>DS</sub> Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I <sub>D</sub> = - 250 μA		- 29		mV/°C			
V <sub>GS(th)</sub> Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	1Β = - 250 μΑ		4.3					
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1.2		- 2.2	V			
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA			
Zoro Coto Voltago Droin Current	1	V <sub>DS</sub> = - 40 V, V <sub>GS</sub> = 0 V			- 1				
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = - 40 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C			- 10	μΑ			
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \le -5 \text{ V}, V_{GS} = -10 \text{ V}$	- 20			Α			
	Ъ	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 4.4 A		0.039	0.047	Ω			
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = -4.5 \text{ V}, I_D = -3.7 \text{ A}$		0.053	0.065				
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 4.4 A		13		S			
Dynamic <sup>b</sup>									
Input Capacitance	C <sub>iss</sub>			890					
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> = - 20 V, V <sub>GS</sub> = 0 V, f = 1 MHz		115		pF			
Reverse Transfer Capacitance	C <sub>rss</sub>			95					
Total Oata Observe		$V_{DS} = -20 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -4.9 \text{ A}$		22	35	nC			
Total Gate Charge	$Q_g$			11	17				
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = -20 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -4.9 \text{ A}$		2.9					
Gate-Drain Charge	Q <sub>gd</sub>			5.2					
Gate Resistance	$R_g$	f = 1 MHz	1.4	7.2	14.4	Ω			
Turn-On Delay Time	t <sub>d(on)</sub>			40	80				
Rise Time	t <sub>r</sub>	$V_{DD}$ = - 20 V, $R_L$ = 5.1 $\Omega$		30	60				
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong$ - 3.9 A, $V_{GEN}$ = - 4.5 V, $R_g$ = 1 $\Omega$		30	60				
Fall Time	t <sub>f</sub>			12	25	no			
Turn-On Delay Time	t <sub>d(on)</sub>			7	15	ns			
Rise Time	t <sub>r</sub>	$V_{DD}$ = - 20 V, $R_L$ = 5.1 $\Omega$		12	25				
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong$ - 3.9 A, $V_{GEN}$ = - 10 V, $R_g$ = 1 $\Omega$		30	60				
Fall Time	t <sub>f</sub>			10	20				
Drain-Source Body Diode Characteristics									
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C			- 12	۸			
Pulse Diode Forward Current	I <sub>SM</sub>				- 30	A			
Body Diode Voltage	$V_{SD}$	I <sub>S</sub> = - 3.9 A, V <sub>GS</sub> = 0 V		- 0.8	- 1.2	V			
Body Diode Reverse Recovery Time	t <sub>rr</sub>			25	50	ns			
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>F</sub> = - 3.9 A, dI/dt = 100 A/μs, T <sub>.I</sub> = 25 °C		22	50	nC			
Reverse Recovery Fall Time	t <sub>a</sub>	$_{1F} = -3.8 \text{ A}, \text{ u/u} = 100 \text{ A/} \mu \text{s}, \text{ I}_{J} = 25 \text{ C}$		17					
Reverse Recovery Rise Time	t <sub>b</sub>			8		ns			

### Notes:

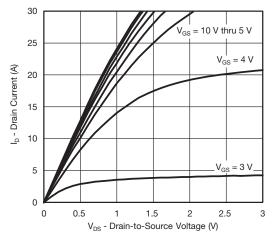
- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

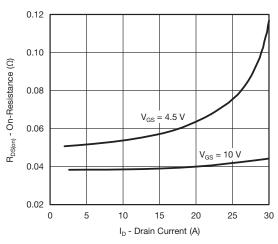




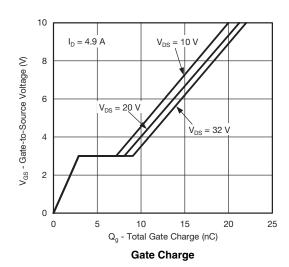
### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

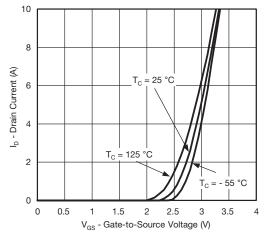


### **Output Characteristics**

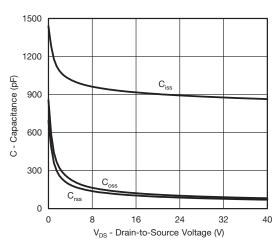


On-Resistance vs. Drain Current and Gate Voltage

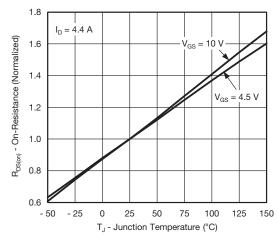




**Transfer Characteristics** 

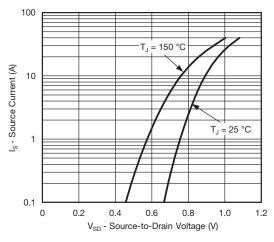


Capacitance

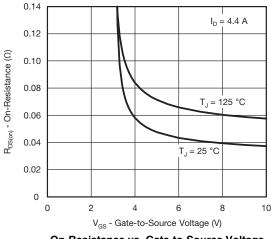


On-Resistance vs. Junction Temperature

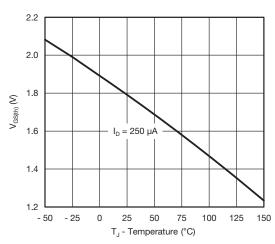
### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



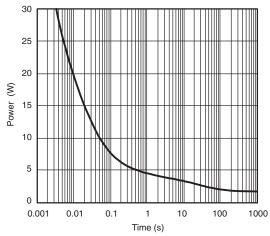
Soure-Drain Diode Forward Voltage



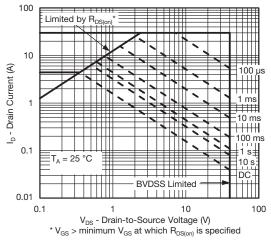
On-Resistance vs. Gate-to-Source Voltage



**Threshold Voltage** 



Single Pulse Power, Junction-to-Ambient

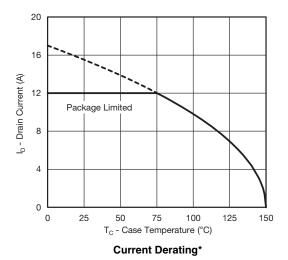


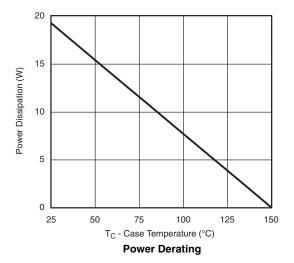
Safe Operating Area, Junction-to-Ambient





### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

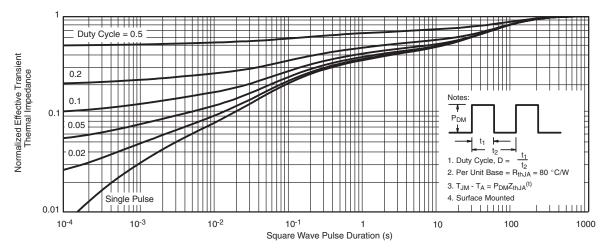




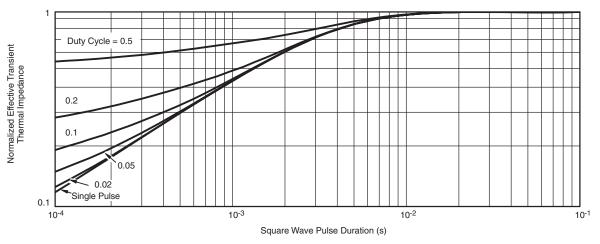
<sup>\*</sup> The power dissipation  $P_D$  is based on  $T_{J(max.)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



### Normalized Thermal Transient Impedance, Junction-to-Ambient



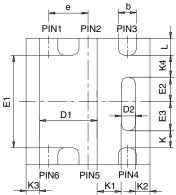
Normalized Thermal Transient Impedance, Junction-to-Case

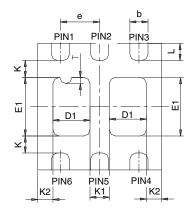
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?63277.





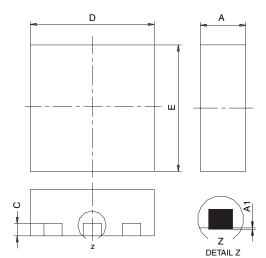
## PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
  Package outline exclusive of mold flash and metal burr
  Package outline inclusive of plating

	SINGLE PAD DUAL PAD											
DIM	M	ILLIMETER	RS		INCHES		M	ILLIMETER	RS		INCHES	
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028
D2	0.135	0.235	0.335	0.005	0.009	0.013						
Е	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041
E2	0.345	0.395	0.445	0.014	0.016	0.018						
E3	0.425	0.475	0.525	0.017	0.019	0.021						
е		0.65 BSC			0.026 BSC	,	0.65 BSC			0.026 BSC		
K		0.275 TYP	1		0.011 TYP		0.275 TYP			0.011 TYP		
K1		0.400 TYP 0.016 TYP		0.320 TYP			0.013 TYP					
K2		0.240 TYP 0.009 TYP		0.252 TYP			0.010 TYP					
К3		0.225 TYP	1	0.009 TYP								
K4		0.355 TYP 0.014 TYP										
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015
Т							0.05	0.10	0.15	0.002	0.004	0.006
ECNI- C C	7404 D	. 0 00 1	. 07									

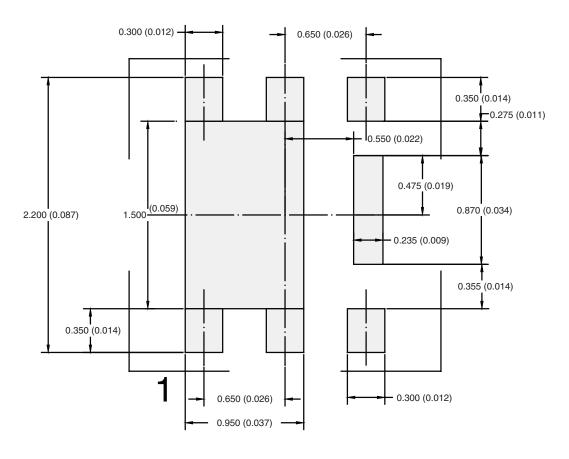
ECN: C-07431 - Rev. C, 06-Aug-07

DWG: 5934

Document Number: 73001 06-Aug-07



## RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Single



Dimensions in mm/(Inches)

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ATTLICATION NOT



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Vishay

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